



INITIAL PRODUCT/PROCESS CHANGE NOTIFICATION
Generic Copy

15-Mar-2007

SUBJECT: ON Semiconductor Initial Product/Process Change Notification #15744

TITLE: Additional P Channel Trench Wafer Capacity at Aizu

PROPOSED FIRST SHIP DATE: 15-July-2007

AFFECTED CHANGE CATEGORY: ON Semiconductor Wafer Fab Site

AFFECTED PRODUCT DIVISION: Power MOSFET Business Unit

FOR ANY QUESTIONS CONCERNING THIS NOTIFICATION:

Contact your local ON Semiconductor Sales Office or Jennie Shen < Jennie.Shen@onsemi.com >

SAMPLES: Contact your local ON Semiconductor Sales Office or Sam Abdeh < sam.abdeh@onsemi.com >

ADDITIONAL RELIABILITY DATA: Available

Contact your local ON Semiconductor Sales Office or Donna Scheuch < d.scheuch@onsemi.com >

NOTIFICATION TYPE:

Initial Product/Process Change Notification (IPCN)

First change notification sent to customers. IPCNs are issued at least 120 days prior to implementation of the change. An IPCN is advance notification about an upcoming change and contains general information regarding the change details and devices affected. It also contains the preliminary reliability qualification plan.

The completed qualification and characterization data will be included in the Final Product/Process Change Notification (FPCN).

This IPCN notification will be followed by a Final Product/Process Change Notification (FPCN) at least 60 days prior to implementation of the change.

DESCRIPTION AND PURPOSE:

ON Semiconductor is pleased to announce the addition of wafer fabrication capacity for the P-channel Trench MOSFET technology platform, in ON Semiconductor's Internal Fab in Aizu, Japan. The facility is an already qualified site for the N-channel Trench and the High Cell Density Planar wafer technologies. Final PCNs will be released at completion of the Reliability data.

**Initial Product/Process Change Notification #15744****QUALIFICATION PLAN:**

Test: High Temperature Reverse Bias (HTRB) Group 1
Conditions: Vds= 80% Vds rating, Ta=150°C, 504-Hrs

Test: High Temperature Reverse Bias (HTRB) Group 2
Conditions: Vds= 80% Vds rating, Ta=150°C, 504-Hrs

Test: High Temperature Gate Bias (HTGB) Group 1
Conditions: Vgs= 100%Vgs, Ta=150°C, 504-Hrs.

Test: High Temperature Gate Bias (HTGB) Group 2
Conditions: Vgs= 100%Vgs, Ta=150°C, 504-Hrs.

Test: Intermittent Operating Life (IOL-PC)
Conditions: Ta=+25°C, delta Tj=100°C, 2-min on/off, 7.5K-cycles

Test: Temperature Cycling (TC-PC)
Conditions: Ta=-65°C/+150°C, Air-to-Air, Dwell >=10-min, 500-cy

Test: Highly Accelerated Stress Test (HAST-PC)
Conditions: Ta=130°C, RH=85%, P=18.8psig, 96-Hrs

Test: Highly Accelerated Stress Test (HAST-PC)
Conditions: Ta=121°C, RH=100%, P=15psig, 96-Hrs

AFFECTED DEVICE LIST:**PART**

NTMFS4122NT1G
NTS2101PT1G
NTS4101PT1G
NTMFS4122NT3G
NTS2101PT1
NTS4101PT1
NTHD3100CT1G
NTA4151PT1G
NTZS3151PT1G
NTHD3100CT1
NTA4151PT1
NTZS3151PT5G
NTHD3100CT3G
NTE4151PT1G
NTHD3100CT3
NTE4151PT1
NTGD1100LT1G
NTHD3101FT1G
NTGD1100LT1
NTHD3101FT1
NTZD3152PT1G
NTHD3101FT3G
NTZD3152PT2G
NTJS3151PT1G
NTHD3101FT3



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NTZD3152PT5G
NTJS3151PT1
NTHD4102PT1G
NTZD3155CT1G
NTJS3151PT2G
NTHD4102PT1
NTZD3155CT2G
NTJS3151PT2
NUS2045MNT1G
NTZD3155CT5G
NUS2045MNT1
NTR2101PT1G
NTR4101PT1G
NTHD2102PT1G
NTR2101PT1
NTR4101PT1
NTHD2102PT1
NTZD3154NT1G
NTHD4102PT3G
NTHD5904NT1G
NTZD3154NT2G
NTHD5904NT1
NTZD3154NT5G
NTHS4101PT1G
NTHD5904NT3G
NTZD3155CT1G
NTHS4101PT1
NTHD5904NT3
NTZD3155CT2G
STHS4101PT1G
NTZD3155CT5G
STHS4101PT1
NTJS3157NT1G
NTA4153NT1G
NTJS4151PT1G
NTJS3157NT1
NTA4153NT1
NTJS4151PT1
NTJS3157NT2G
NTE4153NT1G
NTJS3157NT2
NTE4153NT1
NTJS3157NT4G
NTJS3157NT4
NTHD3102CT1G
NTJD2152PT1G
NTHS2101PT1G
NTJD2152PT1
NTHS2101PT1
NTJD2152PT2G
NTJD2152PT2
NTK3142PT1G
NTJD4105CT1G
NTK3142PT5G
NTJD4105CT1
NTJD4105CT2G



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NTJD1155LT1G
NTJD4105CT2
NTJD1155LT1
NTJD4105CT4G
NTJD1155LT1G
NTJD4105CT4
NTJD1155LT1
NTJD2152PT1G
NTJD2152PT1
NTJD4152PT1G
NTJD2152PT2G
NTJD4152PT1
NTJD2152PT2
NTJD4158CT1G
NTJD4105CT1G
NTJD4158CT2G
NTJD4105CT1
NTJD4152PT1G
NTJD4105CT2G
NTJD4152PT1
NTJD4105CT2
NTJD4105CT4G
NTMFS4121NT1G
NTJD4105CT4
NTMFS4121NT3G